# Medium Power Transistor (32V, 0.8A) **2SD1781K**

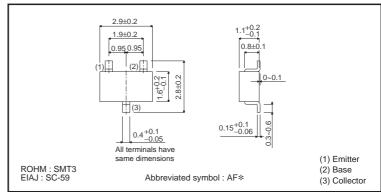
#### Features

- 1) Very Low VcE(sat). VcE(sat) = -0.1V(Typ.) (Ic / Ib= 500mA / 50mA)
- 2) High current capacity in compact package.
- 3) Complements the 2SB1197K.

#### Structure

Epitaxial planar type NPN silicon transistor

# ●External dimensions (Unit : mm)



<sup>\*</sup> Denotes hre

# ● Absolute maximum ratings (Ta=25°C)

| Parameter                   | Symbol | Limits      | Unit        |
|-----------------------------|--------|-------------|-------------|
| Collector-base voltage      | Vсво   | 40          | V           |
| Collector-emitter voltage   | Vceo   | 32          | V           |
| Emitter-base voltage        | VEBO   | 5           | V           |
| Collector current           | lc     | 0.8         | A (DC)      |
|                             | Іср    | 1.5         | A (Pulse) * |
| Collector power dissipation | Pc     | 200         | mW          |
| Junction temperature        | Tj     | 150         | °C          |
| Storage temperature         | Tstg   | -55 to +150 | °C          |

<sup>\*</sup> Single pulse Pw=100ms

## ●Electrical characteristics (Ta=25°C)

| Parameter                            | Symbol   | Min. | Тур. | Max. | Unit | Conditions                    |
|--------------------------------------|----------|------|------|------|------|-------------------------------|
| Collector-base breakdown voltage     | ВУсво    | 40   | -    | -    | V    | Ic=50μA                       |
| Collector-emitter breakdown voltage  | BVceo    | 32   | -    | -    | V    | Ic=1mA                        |
| Emitter-base breakdown voltage       | ВУево    | 5    | _    | -    | V    | Iε=50μA                       |
| Collector cutoff current             | Ісво     | -    | -    | 0.5  | μΑ   | Vcb=20V                       |
| Emitter cutoff current               | ІЕВО     | -    | -    | 0.5  | μΑ   | V <sub>EB</sub> =4V           |
| Collector-emitter saturation voltage | VCE(sat) | -    | 0.1  | 0.4  | V    | Ic/I <sub>B</sub> =500mA/50mA |
| DC current transfer ratio            | hfe      | 120  | -    | 390  | -    | VcE=3V, Ic=100mA              |
| Transition frequency                 | f⊤       | -    | 150  | -    | MHz  | Vce=5V, Ie= -50mA, f=100MHz   |
| Output capacitance                   | Cob      | _    | 15   | _    | pF   | Vcb=10V, Ie=0A, f=1MHz        |

## ●Packaging specifications and hFE

|          |     | Package                      | Taping |
|----------|-----|------------------------------|--------|
|          |     | Code                         | T146   |
| Туре     | hfe | Basic ordering unit (pieces) | 3000   |
| 2SD1781K | QR  |                              | 0      |

#### hre values are classified as follows:

| Item | Q          | R          |
|------|------------|------------|
| hfe  | 120 to 270 | 180 to 390 |

# •Electrical characteristic curves

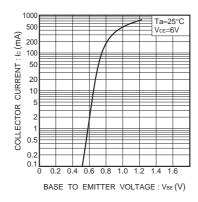


Fig.1 Grounded emitter propagation characteristics

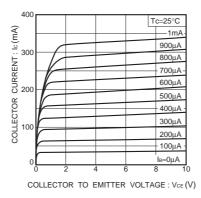


Fig.2 Grounded emitter output characteristics

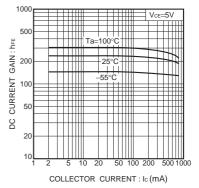


Fig.3 DC current gain vs. collector current

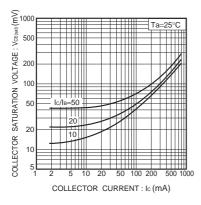


Fig.4 Collector-emitter saturation voltage vs. collector current ( I )

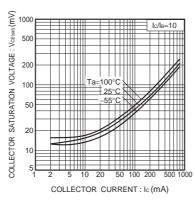


Fig.5 Collector-emitter saturation voltage vs. collector current ( II )

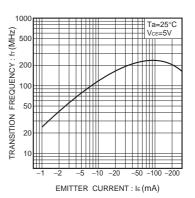


Fig.6 Gain bandwidth product vs. emitter current

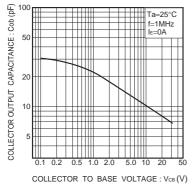


Fig.7 Collector output capacitance vs. collector-base voltage

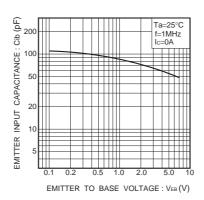


Fig.8 Emitter input capacitance vs. emitter-base voltage

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